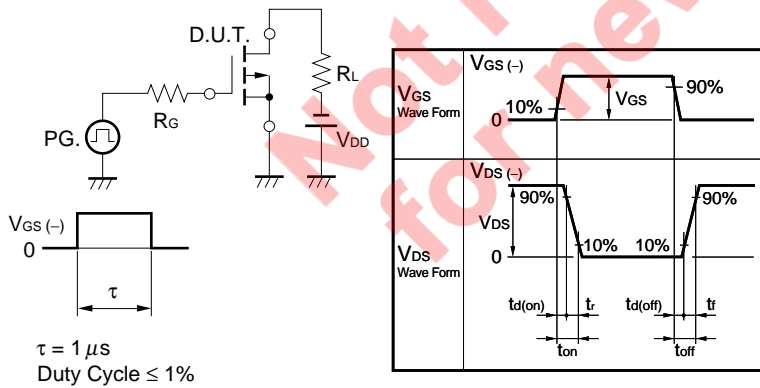


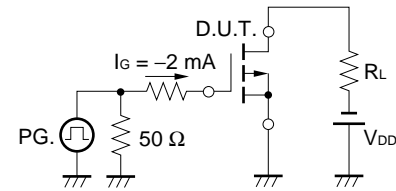
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}$			-10	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \mp 8.0\text{ V}, V_{DS} = 0\text{ V}$			±10	μA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{ V}, I_D = -1.0\text{ mA}$	-0.45		-1.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -2.5\text{ A}$	4.0			S
Drain to Source On-state Resistance	$R_{DS(on)1}$	$V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$		40	50	mΩ
	$R_{DS(on)2}$	$V_{GS} = -2.5\text{ V}, I_D = -2.5\text{ A}$		51	68	mΩ
	$R_{DS(on)3}$	$V_{GS} = -1.8\text{ V}, I_D = -1.5\text{ A}$		68	114	mΩ
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V}$		610		pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$		150		pF
Reverse Transfer Capacitance	C_{rss}	$f = 1.0\text{ MHz}$		100		pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -6.0\text{ V}, I_D = -2.5\text{ A}$		50		ns
Rise Time	t_r	$V_{GS} = -4.0\text{ V}$		200		ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 10\ \Omega$		400		ns
Fall Time	t_f			315		ns
Total Gate Charge	Q_G	$V_{DD} = -10\text{ V}$		5.5		nC
Gate to Source Charge	Q_{GS}	$V_{GS} = -4.0\text{ V}$		1.5		nC
Gate to Drain Charge	Q_{GD}	$I_D = -5.0\text{ A}$		1.6		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 5.0\text{ A}, V_{GS} = 0\text{ V}$		0.89		V

TEST CIRCUIT 1 SWITCHING TIME

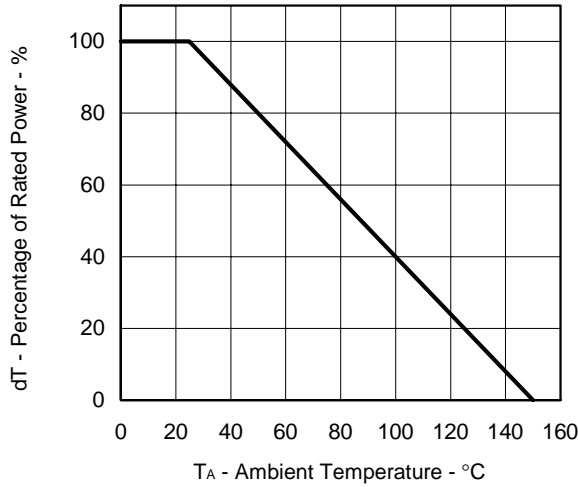


TEST CIRCUIT 2 GATE CHARGE

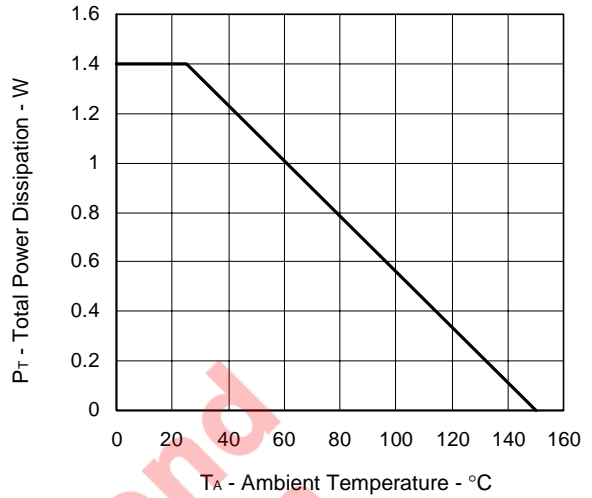


TYPICAL CHARACTERISTICS (T_A = 25°C)

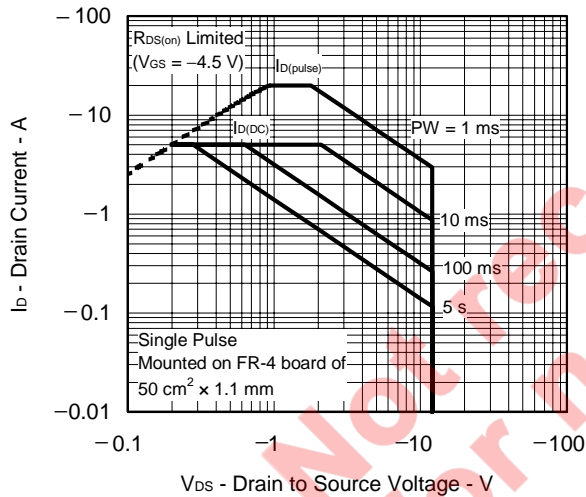
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



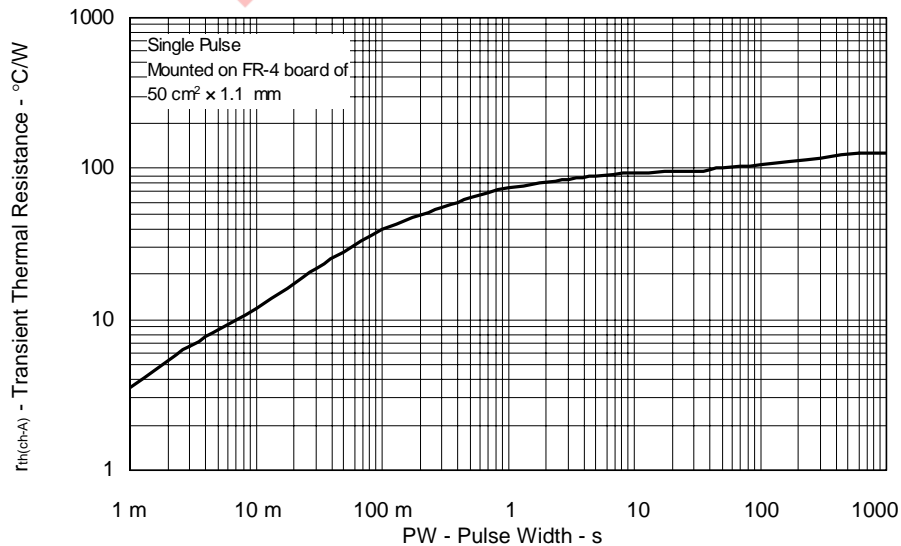
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



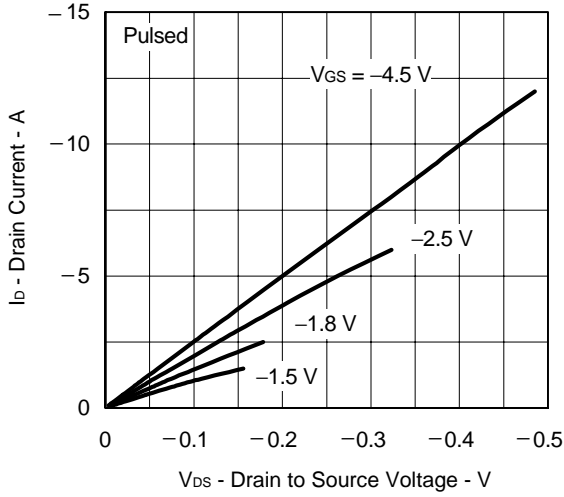
FORWARD BIAS SAFE OPERATING AREA



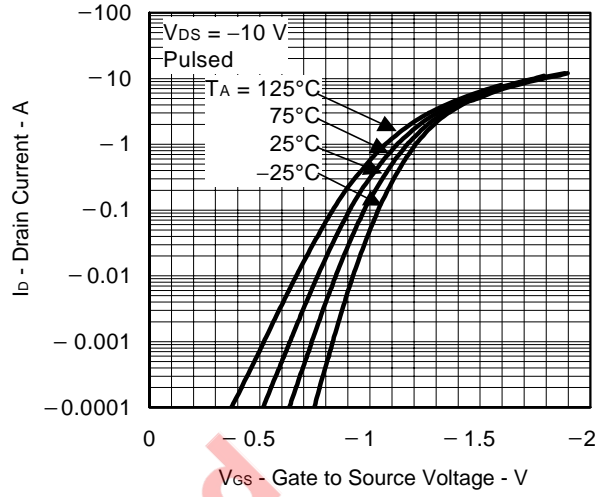
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



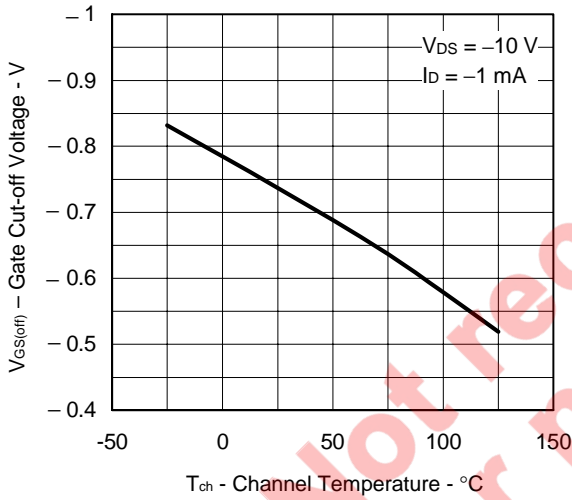
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



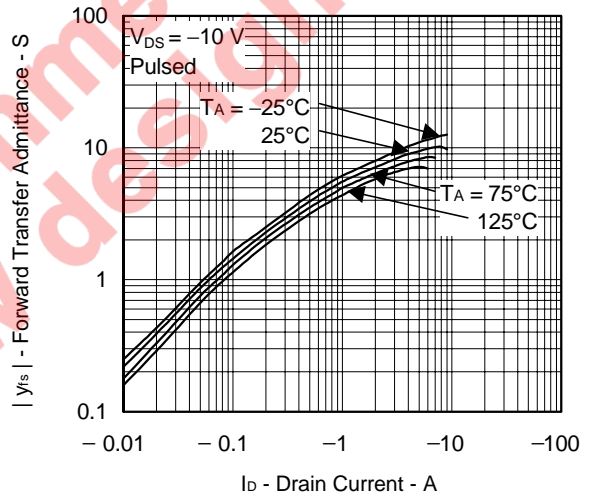
FORWARD TRANSFER CHARACTERISTICS



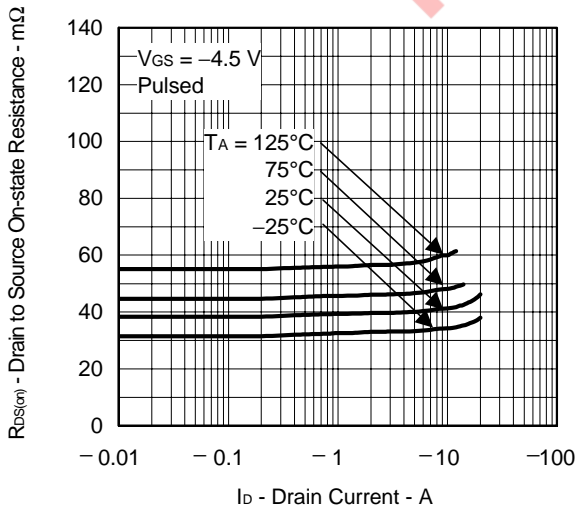
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



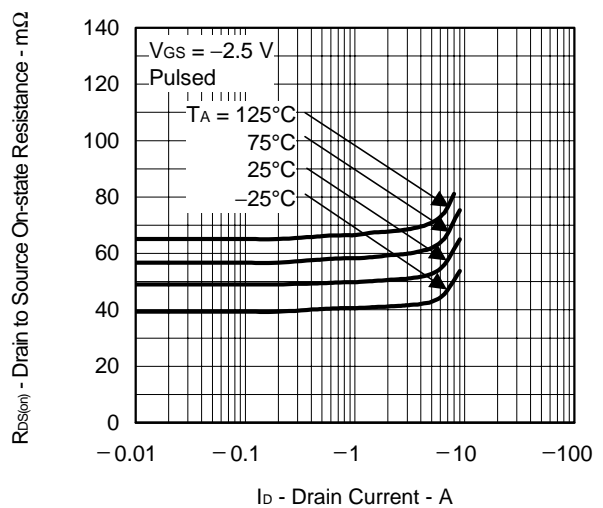
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



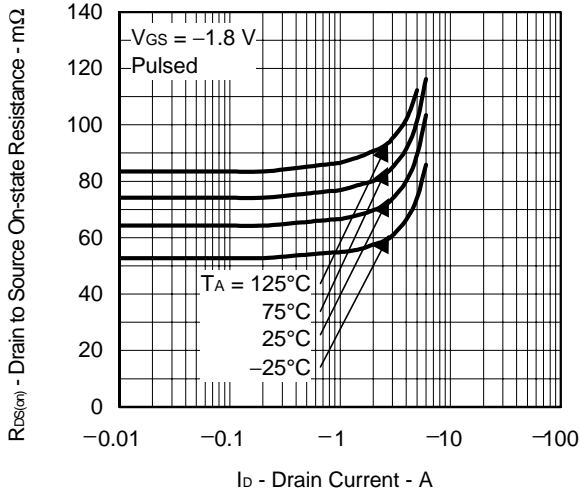
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



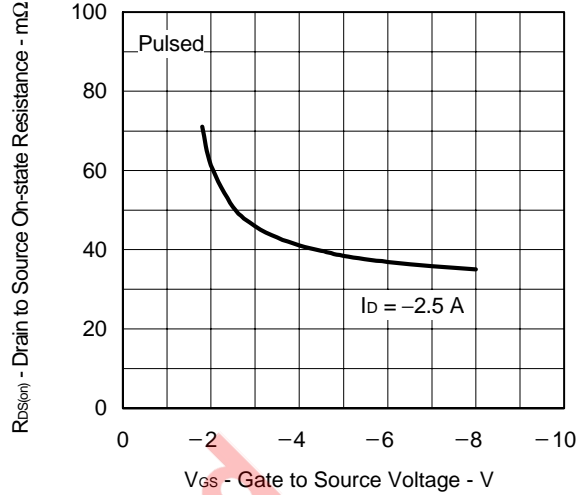
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



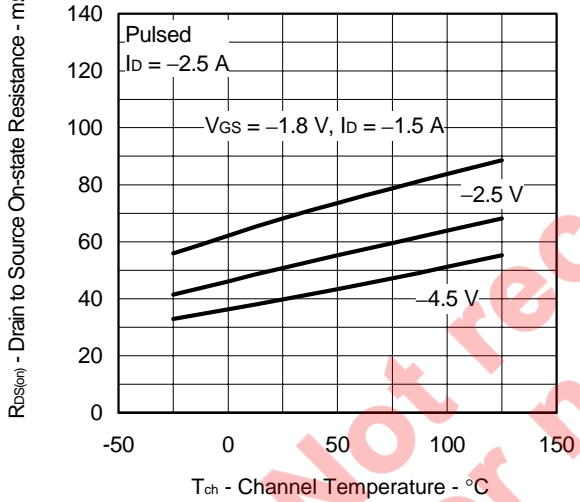
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



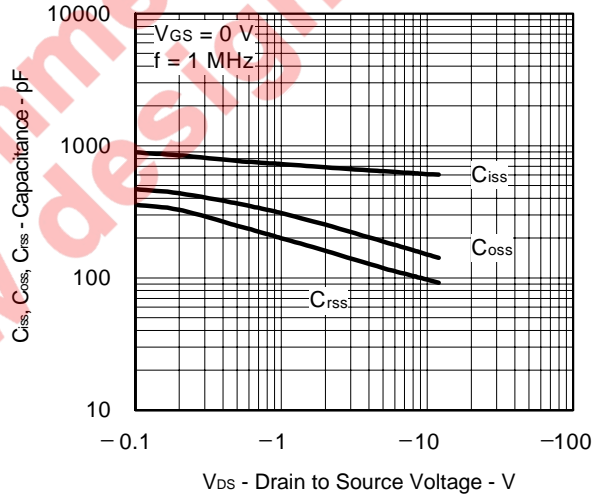
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



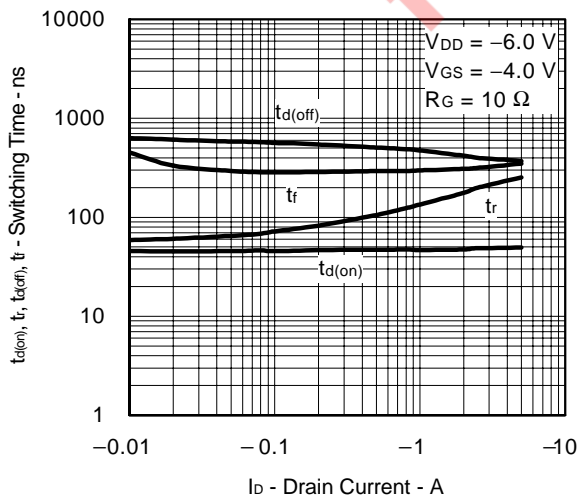
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



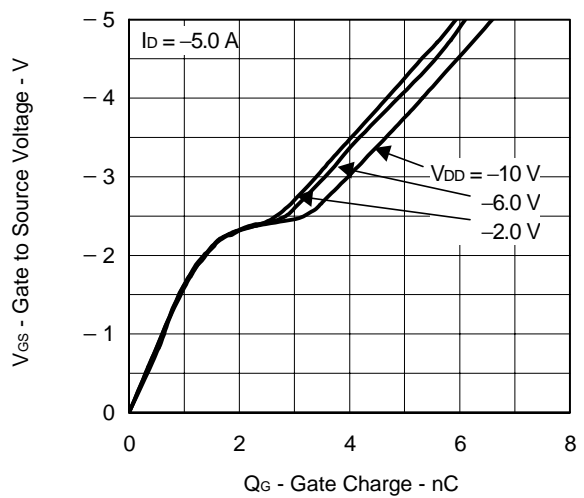
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

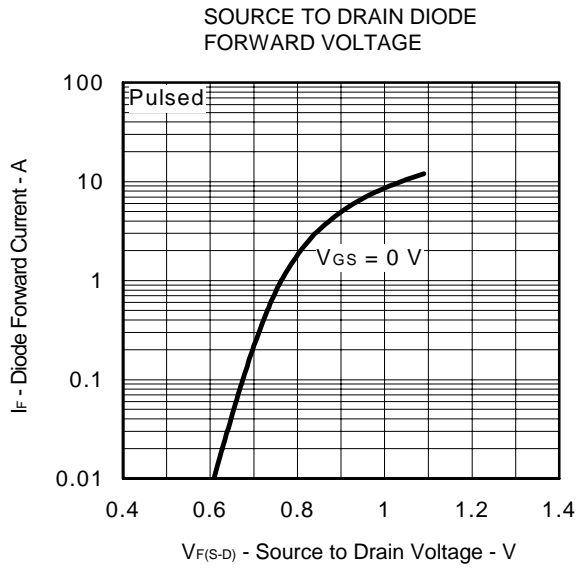


SWITCHING CHARACTERISTICS



DYNAMIC INPUT/OUTPUT CHARACTERISTICS





Not recommend
for new design